

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1778	349/139	US-PGPUB; USPAT; JPO	OR	ON	2003/09/02 15:16
S2	1121	349/138	US-PGPUB; USPAT; JPO	OR	ON	2002/12/19 10:39
S3	240	349/147	US-PGPUB; USPAT; JPO	OR	ON	2002/12/19 10:39
S4	1194	349/149	US-PGPUB; USPAT; JPO	OR	ON	2002/12/19 10:39
S5	284	349/151	US-PGPUB; USPAT; JPO	OR	ON	2002/12/19 10:39
S6	1199	349/153	US-PGPUB; USPAT; JPO	OR	ON	2002/12/19 10:39
S7	202	349/190	US-PGPUB; USPAT; JPO	OR	ON	2002/12/19 10:40
S8	4624	((stack\$4 or lamilat\$4 or multi\$5) with layer\$4) and (insulat\$4 same (semiconduct\$4 or silicon) same protect\$4)	US-PGPUB; USPAT; JPO	OR	ON	2002/12/19 10:56
S9	440	349/139 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain)	US-PGPUB; USPAT; JPO	OR	ON	2002/12/19 11:32
S10	421	((((stack\$4 or lamilat\$4 or multi\$5) with layer\$4) and (insulat\$4 same (semiconduct\$4 or silicon) same protect\$4)) and ((signal adj line) or drain or source or data) and corrosion	US-PGPUB; USPAT; JPO	OR	ON	2002/12/19 11:04
S11	300	349/149 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain)	US-PGPUB; USPAT; JPO	OR	ON	2002/12/19 11:27
S12	35	((((stack\$4 or lamilat\$4 or multi\$5) with layer\$4) and (insulat\$4 same (semiconduct\$4 or silicon) same protect\$4)) and (signal adj line) and corrosion and gap	US-PGPUB; USPAT; JPO	OR	ON	2002/12/19 15:32
S13	24	((((stack\$4 or lamilat\$4 or multi\$5) with layer\$4) and (insulat\$4 same (semiconduct\$4 or silicon) same protect\$4)) and (signal adj line) and corrosion and gap and drive and terminal	US-PGPUB; USPAT; JPO	OR	ON	2002/12/19 15:41

S14	172	349/153 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain)	US-PGPUB; USPAT; JPO	OR	ON	2002/12/20 11:08
S15	57	349/139 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain)and corrosion	US-PGPUB; USPAT; JPO	OR	ON	2002/12/20 11:30
S16	29	349/138 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain)and corrosion	US-PGPUB; USPAT; JPO	OR	ON	2002/12/20 11:49
S17	4	349/190 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain)and corrosion	US-PGPUB; USPAT; JPO	OR	ON	2002/12/20 15:14
S18	20	349/138 and (stack\$4 or laminat\$4 or multi\$5) and (signal adj line) and corrosion	US-PGPUB; USPAT; JPO	OR	ON	2002/12/20 15:17
S19	50	349/149 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain)and corrosion	US-PGPUB; USPAT; JPO	OR	ON	2002/12/20 15:20
S20	145	349/147 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain)	US-PGPUB; USPAT; JPO	OR	ON	2002/12/20 15:34
S21	129	349/151 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain)	US-PGPUB; USPAT; JPO	OR	ON	2002/12/20 15:44
S22	74	((stack\$4 or lamilat\$4 or multi\$5) with layer\$4) and (insulat\$4 same (semiconduct\$4 or silicon) same protect\$4)) and (signal adj line) and corrosion	US-PGPUB; USPAT; JPO	OR	ON	2002/12/20 16:06
S23	42848	(driv\$4 or chip or semiconduct\$) and ((stack\$4 or laminat\$4) with (AS or semiconduct\$4))	USPAT	OR	OFF	2003/08/29 09:33
S24	2884	(driv\$4 or chip or semiconduct\$) and ((stack\$4 or laminat\$4) with (AS or semiconduct\$4)) and (liquid adj crystal)	USPAT	OR	OFF	2003/08/29 09:33
S25	8367	(driv\$4 or chip or semiconduct\$) and ((stack\$4 or laminat\$4) with (AS or semiconduct\$4)) and (liquid adj crystal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/29 10:07
S26	96	(driv\$4 or chip or semiconduct\$) and ((stack\$4 or laminat\$4) with (AS or semiconduct\$4)) and (liquid adj crystal)and 349/149	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/29 09:39

S27	154	(driv\$4 or chip or semiconductor) and ((stack\$4 or laminat\$4) with (AS or semiconductor\$4)) and (liquid adj crystal)and 349/139	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/29 09:59
S28	3245	(driv\$4 or chip or semiconductor) and ((stack\$4 or laminat\$4) with (AS or semiconductor\$4)) and (liquid adj crystal)and terminal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/29 10:08
S29	1329	(driv\$4 or chip or semiconductor) and ((stack\$4 or laminat\$4) with (AS or semiconductor\$4)) and (liquid adj crystal)and terminal and peripheral	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/29 10:10
S30	133	QI.xa.	USPAT	OR	OFF	2003/08/29 10:37
S31	431214	pcb (printed adj circuit) driv\$3 adj circuit IC (integrated adj circuit)	US-PGPUB; USPAT	OR	ON	2003/09/02 15:22
S32	352493	semiconductor	US-PGPUB; USPAT	OR	ON	2003/09/02 15:21
S33	817	(349/149-152).ccls.	US-PGPUB; USPAT	OR	ON	2003/09/02 15:21
S34	284155	pcb (printed adj circuit) driv\$3 adj circuit IC (integrated adj circuit) near10 periphery near10 semiconductor	US-PGPUB; USPAT	OR	ON	2003/09/02 15:24
S35	9	(pcb or (printed adj circuit) or (driv\$3 adj circuit IC) or (integrated adj circuit)) near10 periphery near10 semiconductor and ((349/149-152). ccls.)	US-PGPUB; USPAT	OR	ON	2003/09/02 15:53
S36	399	(pcb or (printed adj circuit) or (driv\$3 adj circuit IC) or (integrated adj circuit)) near10 periphery near10 semiconductor	US-PGPUB; USPAT	OR	ON	2003/09/02 15:47
S37	399	(pcb (printed adj circuit) driv\$3 adj circuit IC (integrated adj circuit)) near10 periphery near10 semiconductor	US-PGPUB; USPAT	OR	ON	2003/09/02 16:56
S38	0	(pcb (printed adj circuit) driv\$3 adj circuit IC (integrated adj circuit)) near10 periphery near10 semiconductor near10 ((stack or laminat\$4) with insulat\$4)	US-PGPUB; USPAT	OR	ON	2003/09/02 16:21
S39	0	(pcb (printed adj circuit) driv\$3 adj circuit IC (integrated adj circuit)) near10 periphery near10 semiconductor near10 ((stack or laminat\$4) near10 insulat\$4)	US-PGPUB; USPAT	OR	ON	2003/09/02 16:28

S40	62	(pcb (printed adj circuit) driv\$3 adj circuit IC (integrated adj circuit)) near10 periphery near10 semiconductor and ((stack or laminat\$4) near10 insulat\$4)	US-PGPUB; USPAT	OR	ON	2003/09/02 16:28
S41	76	(pcb (printed adj circuit) driv\$3 adj circuit IC (integrated adj circuit)) near10 periphery near10 semiconductor and (liquid adj crystal)	US-PGPUB; USPAT	OR	ON	2003/09/02 16:57
S42	1	"6697139".pn.	USPAT	OR	OFF	2004/05/12 15:25
S43	1	"5847781".pn.	USPAT	OR	OFF	2004/05/13 13:37
S44	1	"6590623".pn.	USPAT	OR	ON	2004/08/25 09:15
S45	1	"20040160565".pn.	US-PGPUB	OR	ON	2004/08/25 09:16
S46	12	(pcb or (printed adj circuit) or (driv\$4 adj circuit IC) or (integrated adj circuit)) near10 periphery near10 semiconductor and (349/149-152). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/27 12:50
S47	926	(pcb or (printed adj circuit) or (driv\$4 adj circuit IC) or (integrated adj circuit)) near10 periphery near10 semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/27 12:50
S48	22	(pcb or (printed adj circuit) or (driv\$4 adj circuit IC) or (integrated adj circuit)) near10 periphery near10 semiconductor and "349"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/27 12:51
S49	129	(pcb or (printed adj circuit) or (driv\$4 adj circuit IC) or (integrated adj circuit)) near10 periphery near10 semiconductor and (liquid adj crystal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/27 15:07
S50	4	((signal adj line)near10 extend\$4 near10 peripheral) and (drive adj IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/27 13:44
S51	183	qi.xa.	USPAT	OR	ON	2004/08/27 15:08
S52	579	mike.xa.	USPAT	OR	ON	2004/08/27 15:10
S53	170	(mike and qi).xa.	USPAT	OR	OFF	2004/08/27 15:15